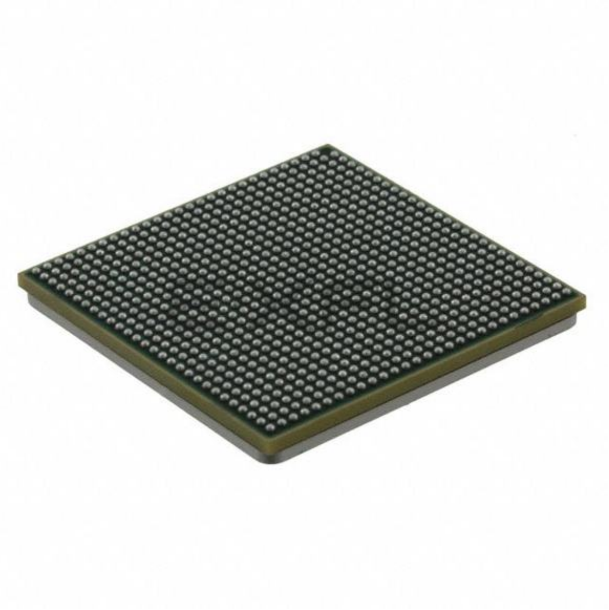

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	Signal Processing; SPE
RAM Controllers	DDR, DDR2, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8547vtaqgd

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the device. This device is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

The following table provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings [1]

Characteristic		Symbol	Max Value	Unit	Notes
Core supply voltage		V_{DD}	–0.3 to 1.21	V	—
PLL supply voltage		AV_{DD}	–0.3 to 1.21	V	—
Core power supply for SerDes transceivers		SV_{DD}	–0.3 to 1.21	V	—
Pad power supply for SerDes transceivers		XV_{DD}	–0.3 to 1.21	V	—
DDR and DDR2 DRAM I/O voltage		GV_{DD}	–0.3 to 2.75 –0.3 to 1.98	V	2
Three-speed Ethernet I/O voltage		LV_{DD} (for eTSEC1 and eTSEC2)	–0.3 to 3.63 –0.3 to 2.75	V	3
		TV_{DD} (for eTSEC3 and eTSEC4)	–0.3 to 3.63 –0.3 to 2.75		
PCI/PCI-X, DUART, system control and power management, I^2C, Ethernet MII management, and JTAG I/O voltage		OV_{DD}	–0.3 to 3.63	V	—
Local bus I/O voltage		BV_{DD}	–0.3 to 3.63 –0.3 to 2.75	V	—
Input voltage	DDR/DDR2 DRAM signals	MV_{IN}	–0.3 to (GV_{DD} + 0.3)	V	4
	DDR/DDR2 DRAM reference	MV_{REF}	–0.3 to (GV_{DD}/2 + 0.3)	V	—
	Three-speed Ethernet I/O signals	LV_{IN} TV_{IN}	–0.3 to (LV_{DD} + 0.3) –0.3 to (TV_{DD} + 0.3)	V	4
	Local bus signals	BV_{IN}	–0.3 to (BV_{DD} + 0.3)	—	—
	DUART, SYSCLK, system control and power management, I^2C, Ethernet MII management, and JTAG signals	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	4
	PCI/PCI-X	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	4

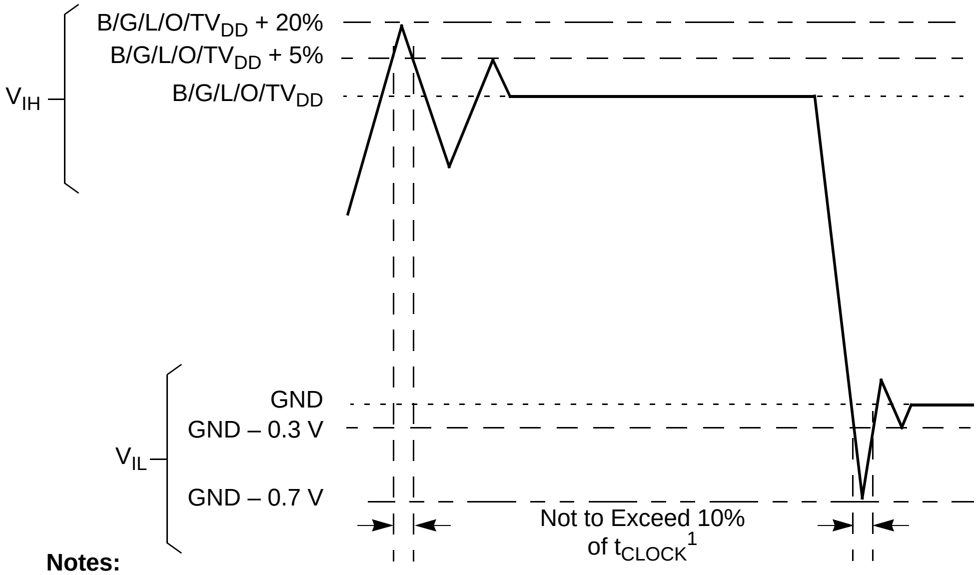
Table 2. Recommended Operating Conditions (continued)

Characteristic	Symbol	Recommended Value	Unit	Notes
Junction temperature range	Tj	0 to 105	°C	—

Notes:

1. This voltage is the input to the filter discussed in Section 22.2, “PLL Power Supply Filtering,” and not necessarily the voltage at the AV_{DD} pin, which may be reduced from V_{DD} by the filter.
2. **Caution:** MV_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
3. **Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
4. **Caution:** L/TV_{IN} must not exceed L/TV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.

The following figure shows the undershoot and overshoot voltages at the interfaces of this device.



Notes:

1. t_{CLOCK} refers to the clock period associated with the respective interface:
   For I^2C and JTAG, t_{CLOCK} references SYSCLK.
   For DDR, t_{CLOCK} references MCLK.
   For eTSEC, t_{CLOCK} references EC_GTX_CLK125.
   For LBIU, t_{CLOCK} references LCLK.
   For PCI, t_{CLOCK} references PCI*n*_CLK or SYSCLK.
   For SerDes, t_{CLOCK} references SD_REF_CLK.
2. Note that with the PCI overshoot allowed (as specified above), the device does not fully comply with the maximum AC ratings and device protection guideline outlined in the PCI rev. 2.2 standard (section 4.2.2.3).

Figure 2. Overshoot/Undershoot Voltage for $GV_{DD}/OV_{DD}/LV_{DD}/BV_{DD}/TV_{DD}$

The core voltage must always be provided at nominal 1.1 V. Voltage to the processor interface I/Os are provided through separate sets of supply pins and must be provided at the voltages shown in Table 2. The input voltage threshold scales with respect to the associated I/O supply voltage. OV_{DD} and LV_{DD} based receivers are simple CMOS I/O circuits and satisfy appropriate LVCMOS type specifications. The DDR SDRAM interface uses a single-ended differential receiver referenced the externally supplied MV_{REF} signal (nominally set to $GV_{DD}/2$) as is appropriate for the SSTL2 electrical signaling standard.

2.1.3 Output Driver Characteristics

The following table provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 3. Output Drive Capability

Driver Type	Programmable Output Impedance (Ω)	Supply Voltage	Notes
Local bus interface utilities signals	25 25	BV_{DD} = 3.3 V BV_{DD} = 2.5 V	1
	45(default) 45(default)	BV_{DD} = 3.3 V BV_{DD} = 2.5 V	
PCI signals	25	OV_{DD} = 3.3 V	2
	45(default)		
DDR signal	18 36 (half strength mode)	GV_{DD} = 2.5 V	3
DDR2 signal	18 36 (half strength mode)	GV_{DD} = 1.8 V	3
TSEC/10/100 signals	45	L/TV_{DD} = 2.5/3.3 V	—
DUART, system control, JTAG	45	OV_{DD} = 3.3 V	—
I2C	150	OV_{DD} = 3.3 V	—

Notes:

1. The drive strength of the local bus interface is determined by the configuration of the appropriate bits in PORIMPSCR.
2. The drive strength of the PCI interface is determined by the setting of the $\overline{\text{PCI\_GNT1}}$ signal at reset.
3. The drive strength of the DDR interface in half-strength mode is at T_j = 105°C and at GV_{DD} (min).

2.2 Power Sequencing

The device requires its power rails to be applied in a specific sequence in order to ensure proper device operation. These requirements are as follows for power-up:

1. V_{DD}, AV_{DD}_*n*, BV_{DD}, LV_{DD}, OV_{DD}, SV_{DD}, TV_{DD}, XV_{DD}
2. GV_{DD}

All supplies must be at their stable values within 50 ms.

NOTE

Items on the same line have no ordering requirement with respect to one another. Items on separate lines must be ordered sequentially such that voltage rails on a previous step must reach 90% of their value before the voltage rails on the current step reach 10% of theirs.

NOTE

In order to guarantee MCKE low during power-up, the above sequencing for GV_{DD} is required. If there is no concern about any of the DDR signals being in an indeterminate state during power-up, then the sequencing for GV_{DD} is not required.

Table 13 provides the recommended operating conditions for the DDR SDRAM controller when GV_{DD}(typ) = 2.5 V.

Table 13. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} – 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.15$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	–0.3	$MV_{REF} – 0.15$	V	—
Output leakage current	I_{OZ}	–50	50	μA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–16.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	16.2	—	mA	—

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM V_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail must track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, $0 V \leq V_{OUT} \leq GV_{DD}$.

Table 14 provides the DDR I/O capacitance when GV_{DD}(typ) = 2.5 V.

Table 14. DDR SDRAM Capacitance for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

This table provides the current draw characteristics for MV_{REF}.

Table 15. Current Draw Characteristics for MV_{REF}

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Current draw for MV_{REF}	I_{MVREF}	—	500	μA	1

Note:

1. The voltage regulator for MV_{REF} must be able to supply up to 500 μA current.

Table 41 describes the timing parameters of the local bus interface at $BV_{DD} = 2.5$ V.

Table 41. Local Bus Timing Parameters (BV_{DD} = 2.5 V)—PLL Enabled

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	7.5	12	ns	2
Local bus duty cycle	t_{LBKH}/t_{LBK}	43	57	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	$t_{LBKSKEW}$	—	150	ps	7, 8
Input setup to local bus clock (except $\overline{\text{LGTA}}$/UPWAIT)	$t_{LBIVKH1}$	1.9	—	ns	3, 4
$\overline{\text{LGTA}}$/LUPWAIT input setup to local bus clock	$t_{LBIVKH2}$	1.8	—	ns	3, 4
Input hold from local bus clock (except $\overline{\text{LGTA}}$/LUPWAIT)	$t_{LBIXKH1}$	1.1	—	ns	3, 4
$\overline{\text{LGTA}}$/LUPWAIT input hold from local bus clock	$t_{LBIXKH2}$	1.1	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH hold time)	t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKHOV1}$	—	2.1	ns	—
Local bus clock to data valid for LAD/LDP	$t_{LBKHOV2}$	—	2.3	ns	3
Local bus clock to address valid for LAD	$t_{LBKHOV3}$	—	2.4	ns	3
Local bus clock to LALE assertion	$t_{LBKHOV4}$	—	2.4	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKHOX1}$	0.8	—	ns	3
Output hold from local bus clock for LAD/LDP	$t_{LBKHOX2}$	0.8	—	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$t_{LBKHOZ1}$	—	2.6	ns	5
Local bus clock to output high impedance for LAD/LDP	$t_{LBKHOZ2}$	—	2.6	ns	5

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.
3. All signals are measured from $BV_{DD}/2$ of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to $0.4 \times BV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is programmed with the LBCR[AHD] parameter.
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $BV_{DD}/2$.
8. Guaranteed by design.

Figure 22 provides the AC test load for the local bus.

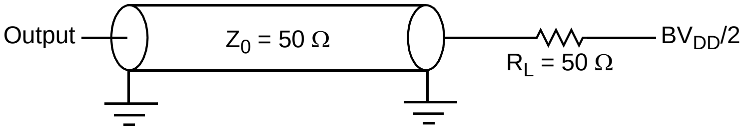


Figure 22. Local Bus AC Test Load

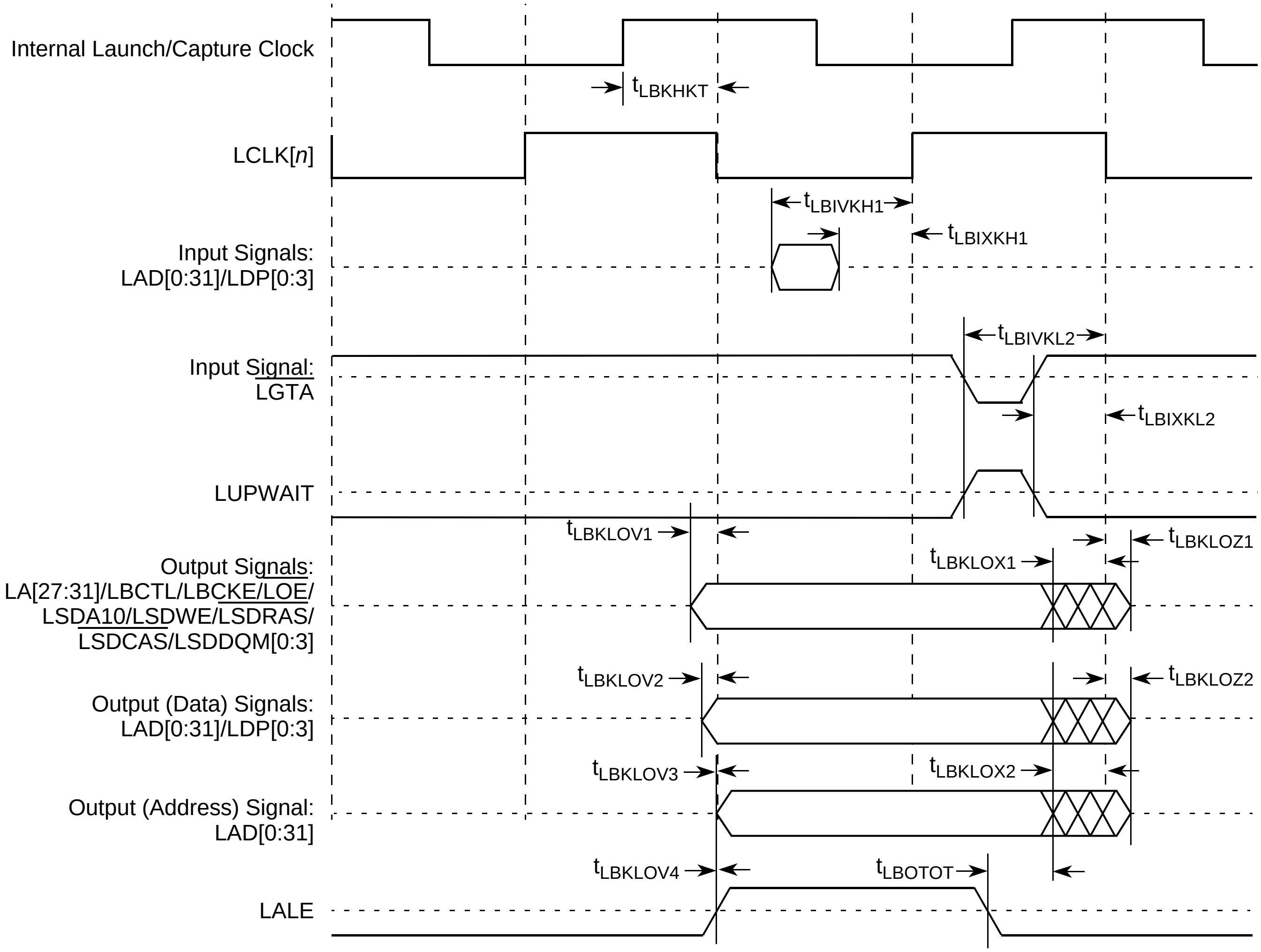


Figure 24. Local Bus Signals (PLL Bypass Mode)

NOTE

In PLL bypass mode, LCLK[*n*] is the inverted version of the internal clock with the delay of t_{LBKHKT}. In this mode, signals are launched at the rising edge of the internal clock and are captured at falling edge of the internal clock with the exception of $\overline{\text{LGTA}}$/LUPWAIT (which is captured on the rising edge of the internal clock).

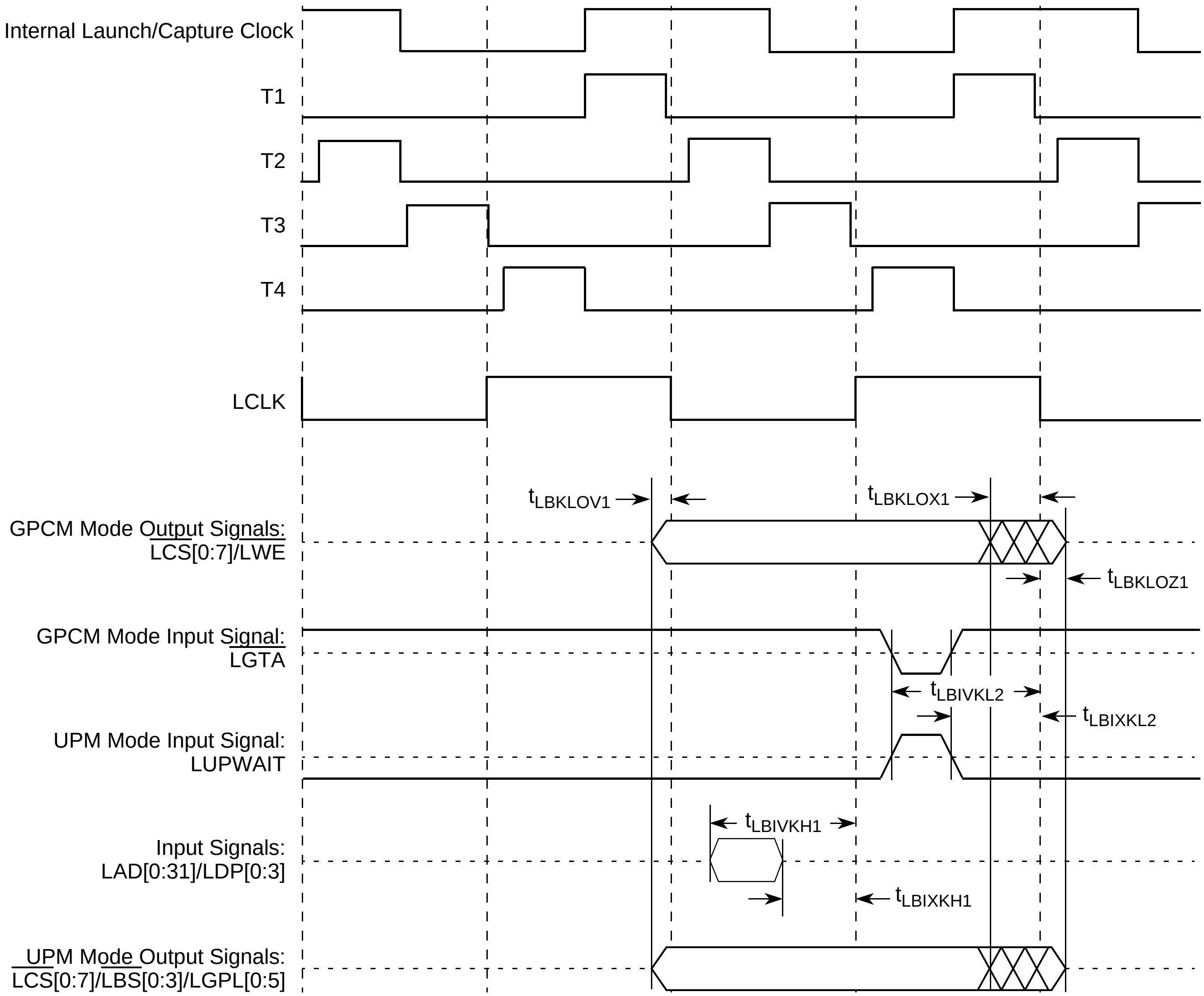


Figure 28. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 8 or 16 (PLL Bypass Mode)

14 GP_{OUT}/GP_{IN}

This section describes the DC and AC electrical specifications for the GP_{OUT}/GP_{IN} bus of the device.

14.1 GP_{OUT}/GP_{IN} Electrical Characteristics

Table 47 and Table 48 provide the DC electrical characteristics for the GP_{OUT} interface.

Table 47. GP_{OUT} DC Electrical Characteristics (3.3 V DC)

Parameter	Symbol	Min	Max	Unit
Supply voltage 3.3 V	BV_{DD}	3.13	3.47	V
High-level output voltage (BV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	BV_{DD} – 0.2	—	V
Low-level output voltage (BV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.2	V

Table 48. GP_{OUT} DC Electrical Characteristics (2.5 V DC)

Parameter	Symbol	Min	Max	Unit
Supply voltage 2.5 V	BV_{DD}	2.37	2.63	V
High-level output voltage (BV_{DD} = min, I_{OH} = –1 mA)	V_{OH}	2.0	BV_{DD} + 0.3	V
Low-level output voltage (BV_{DD} min, I_{OL} = 1 mA)	V_{OL}	GND – 0.3	0.4	V

Table 49 and Table 50 provide the DC electrical characteristics for the GP_{IN} interface.

Table 49. GP_{IN} DC Electrical Characteristics (3.3 V DC)

Parameter	Symbol	Min	Max	Unit
Supply voltage 3.3 V	BV_{DD}	3.13	3.47	V
High-level input voltage	V_{IH}	2	BV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (BV_{IN} [1] = 0 V or BV_{IN} = BV_{DD})	I_{IN}	—	±5	μA

Note:

1. The symbol BV_{IN}, in this case, represents the BV_{IN} symbol referenced in Table 1.

Figure 36 shows the PCI/PCI-X input AC timing conditions.

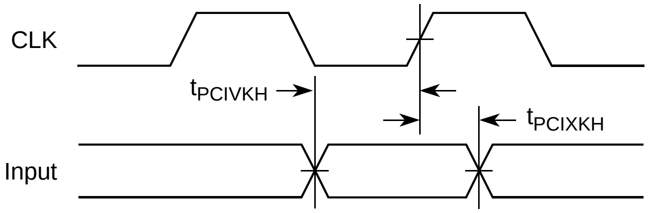


Figure 36. PCI/PCI-X Input AC Timing Measurement Conditions

Figure 37 shows the PCI/PCI-X output AC timing conditions.

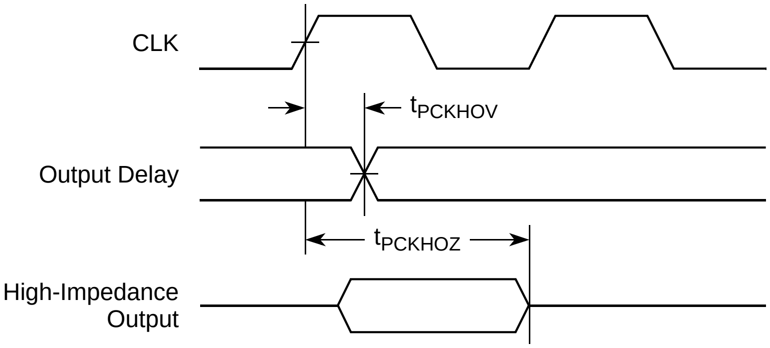


Figure 37. PCI/PCI-X Output AC Timing Measurement Condition

Table 53 provides the PCI-X AC timing specifications at 66 MHz.

Table 53. PCI-X AC Timing Specifications at 66 MHz

Parameter	Symbol	Min	Max	Unit	Notes
SYSCLK to signal valid delay	t_{PCKHOV}	—	3.8	ns	1, 2, 3, 7, 8
Output hold from SYSCLK	t_{PCKHOX}	0.7	—	ns	1, 10
SYSCLK to output high impedance	t_{PCKHOZ}	—	7	ns	1, 4, 8, 11
Input setup time to SYSCLK	t_{PCIVKH}	1.7	—	ns	3, 5
Input hold time from SYSCLK	t_{PCIXKH}	0.5	—	ns	10
$\overline{\text{REQ64}}$ to $\overline{\text{HRESET}}$ setup time	t_{PCRVRH}	10	—	clocks	11
$\overline{\text{HRESET}}$ to $\overline{\text{REQ64}}$ hold time	t_{PCRHRX}	0	50	ns	11
$\overline{\text{HRESET}}$ high to first $\overline{\text{FRAME}}$ assertion	t_{PCRHFV}	10	—	clocks	9, 11
PCI-X initialization pattern to $\overline{\text{HRESET}}$ setup time	t_{PCIVRH}	10	—	clocks	11

  - — The SD_REF_CLK and $\overline{\text{SD\_REF\_CLK}}$ are internally AC-coupled differential inputs as shown in Figure 39. Each differential clock input (SD_REF_CLK or $\overline{\text{SD\_REF\_CLK}}$) has a 50-Ω termination to SGND_SRDS*n* (xcorevss) followed by on-chip AC-coupling.
  - — The external reference clock driver must be able to drive this termination.
  - — The SerDes reference clock input can be either differential or single-ended. See the differential mode and single-ended mode description below for further detailed requirements.
- The maximum average current requirement that also determines the common mode voltage range:
  - — When the SerDes reference clock differential inputs are DC coupled externally with the clock driver chip, the maximum average current allowed for each input pin is 8 mA. In this case, the exact common mode input voltage is not critical as long as it is within the range allowed by the maximum average current of 8 mA (see the following bullet for more detail), since the input is AC-coupled on-chip.
  - — This current limitation sets the maximum common mode input voltage to be less than 0.4 V (0.4 V/50 = 8 mA) while the minimum common mode input level is 0.1 V above SGND_SRDS*n* (xcorevss). For example, a clock with a 50/50 duty cycle can be produced by a clock driver with output driven by its current source from 0 to 16 mA (0–0.8 V), such that each phase of the differential input has a single-ended swing from 0 V to 800 mV with the common mode voltage at 400 mV.
  - — If the device driving the SD_REF_CLK and $\overline{\text{SD\_REF\_CLK}}$ inputs cannot drive 50 Ω to SGND_SRDS*n* (xcorevss) DC, or it exceeds the maximum input current limitations, then it must be AC-coupled off-chip.
- The input amplitude requirement:
  - — This requirement is described in detail in the following sections.

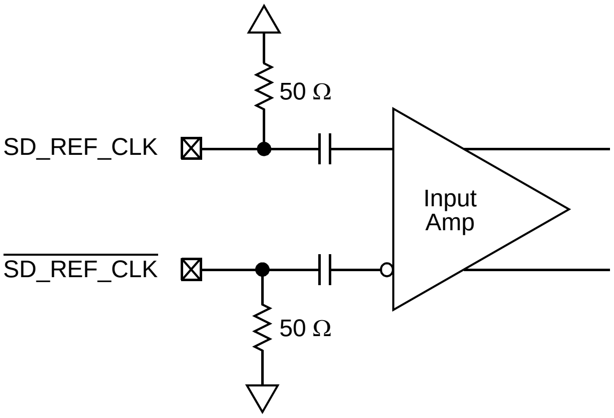


Figure 39. Receiver of SerDes Reference Clocks

16.2.2 DC Level Requirement for SerDes Reference Clocks

The DC level requirement for the SerDes reference clock inputs is different depending on the signaling mode used to connect the clock driver chip and SerDes reference clock inputs as described below:

- Differential mode

16.2.4 AC Requirements for SerDes Reference Clocks

The clock driver selected must provide a high quality reference clock with low phase noise and cycle-to-cycle jitter. Phase noise less than 100 kHz can be tracked by the PLL and data recovery loops and is less of a problem. Phase noise above 15 MHz is filtered by the PLL. The most problematic phase noise occurs in the 1–15 MHz range. The source impedance of the clock driver must be 50 Ω to match the transmission line and reduce reflections which are a source of noise to the system.

The detailed AC requirements of the SerDes reference clocks are defined by each interface protocol based on application usage. See the following sections for detailed information:

- Section 17.2, “AC Requirements for PCI Express SerDes Clocks”
- Section 18.2, “AC Requirements for Serial RapidIO SD_REF_CLK and SD_REF_CLK”

16.2.4.1 Spread Spectrum Clock

SD_REF_CLK/$\overline{\text{SD\_REF\_CLK}}$ are designed to work with a spread spectrum clock (+0% to –0.5% spreading at 30–33 kHz rate is allowed), assuming both ends have same reference clock. For better results, a source without significant unintended modulation must be used.

16.3 SerDes Transmitter and Receiver Reference Circuits

Figure 47 shows the reference circuits for SerDes data lane’s transmitter and receiver.

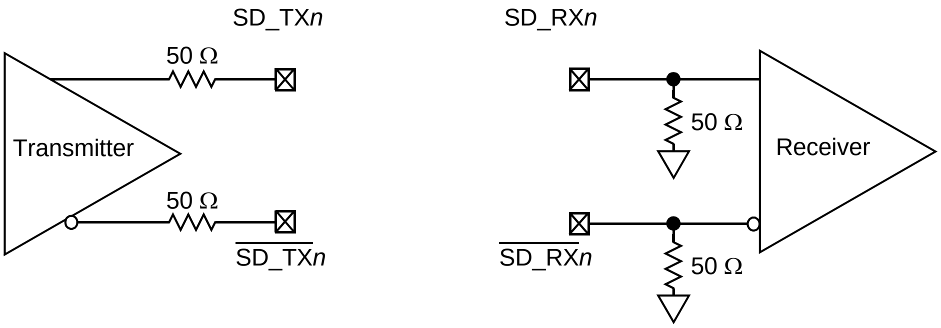


Figure 47. SerDes Transmitter and Receiver Reference Circuits

The DC and AC specification of SerDes data lanes are defined in each interface protocol section below (PCI Express, Serial Rapid IO, or SGMII) in this document based on the application usage:

- Section 17, “PCI Express”
- Section 18, “Serial RapidIO”

Note that external an AC coupling capacitor is required for the above three serial transmission protocols with the capacitor value defined in the specification of each protocol section.

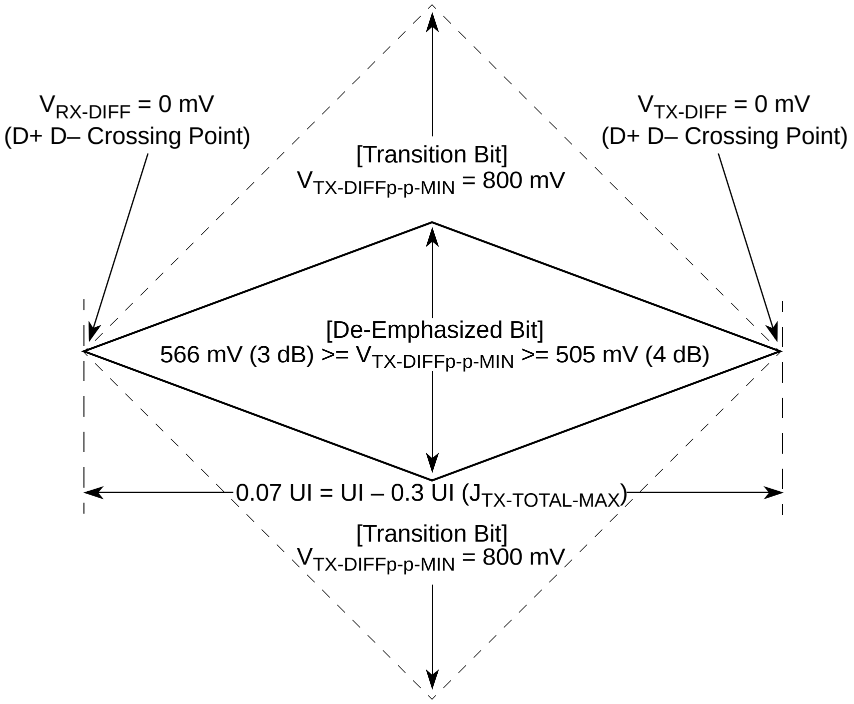


Figure 48. Minimum Transmitter Timing and Voltage Output Compliance Specifications

17.4.3 Differential Receiver (RX) Input Specifications

Table 57 defines the specifications for the differential input at all receivers (RXs). The parameters are specified at the component pins.

Table 57. Differential Receiver (RX) Input Specifications

Symbol	Parameter	Min	Nom	Max	Unit	Comments
UI	Unit interval	399.88	400	400.12	ps	Each UI is 400 ps ± 300 ppm. UI does not account for spread spectrum clock dictated variations. See Note 1.
$V_{RX\text{-}DIFFp\text{-}p}$	Differential peak-to-peak input voltage	0.175	—	1.200	V	$V_{RX\text{-}DIFFp\text{-}p} = 2 \times \lvert V_{RX\text{-}D+} - V_{RX\text{-}D-} \rvert$. See Note 2.
$T_{RX\text{-}EYE}$	Minimum receiver eye width	0.4	—	—	UI	The maximum interconnect media and transmitter jitter that can be tolerated by the receiver can be derived as $T_{RX\text{-}MAX\text{-}JITTER} = 1 - T_{RX\text{-}EYE} = 0.6$ UI. See Notes 2 and 3.
$T_{RX\text{-}EYE\text{-}MEDIAN\text{-}to\text{-}MAX\text{-}JITTER}$	Maximum time between the jitter median and maximum deviation from the median	—	—	0.3	UI	Jitter is defined as the measurement variation of the crossing points ($V_{RX\text{-}DIFFp\text{-}p}$ = 0 V) in relation to a recovered TX UI. A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. Jitter is measured using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI. See Notes 2, 3, and 7.

18.5 Explanatory Note on Transmitter and Receiver Specifications

AC electrical specifications are given for transmitter and receiver. Long- and short-run interfaces at three baud rates (a total of six cases) are described.

The parameters for the AC electrical specifications are guided by the XAUI electrical interface specified in Clause 47 of IEEE 802.3ae-2002.

XAUI has similar application goals to Serial RapidIO, as described in Section 8.1. The goal of this standard is that electrical designs for Serial RapidIO can reuse electrical designs for XAUI, suitably modified for applications at the baud intervals and reaches described herein.

18.6 Transmitter Specifications

LP-serial transmitter electrical and timing specifications are stated in the text and tables of this section.

The differential return loss, S11, of the transmitter in each case shall be better than:

- –10 dB for (baud frequency)/10 < Freq(f) < 625 MHz, and
- –10 dB + 10log(f/625 MHz) dB for 625 MHz ≤ Freq(f) ≤ baud frequency

The reference impedance for the differential return loss measurements is 100-Ω resistive. Differential return loss includes contributions from on-chip circuitry, chip packaging, and any off-chip components related to the driver. The output impedance requirement applies to all valid output levels.

It is recommended that the 20%–80% rise/fall time of the transmitter, as measured at the transmitter output, in each case have a minimum value 60 ps.

It is recommended that the timing skew at the output of an LP-serial transmitter between the two signals that comprise a differential pair not exceed 25 ps at 1.25 GB, 20 ps at 2.50 GB, and 15 ps at 3.125 GB.

Table 59. Short Run Transmitter AC Timing Specifications—1.25 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Output voltage	V_O	–0.40	2.30	V	Voltage relative to COMMON of either signal comprising a differential pair
Differential output voltage	V_{DIFFPP}	500	1000	mV p-p	—
Deterministic jitter	J_D	—	0.17	UI p-p	—
Total jitter	J_T	—	0.35	UI p-p	—
Multiple output skew	S_{MO}	—	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit Interval	UI	800	800	ps	±100 ppm

Table 60. Short Run Transmitter AC Timing Specifications—2.5 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Output voltage	V_O	–0.40	2.30	V	Voltage relative to COMMON of either signal comprising a differential pair
Differential output voltage	V_{DIFFPP}	500	1000	mV p-p	—
Deterministic jitter	J_D	—	0.17	UI p-p	—
Total jitter	J_T	—	0.35	UI p-p	—
Multiple output skew	S_{MO}	—	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit interval	UI	400	400	ps	±100 ppm

Table 61. Short Run Transmitter AC Timing Specifications—3.125 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Output voltage	V_O	–0.40	2.30	V	Voltage relative to COMMON of either signal comprising a differential pair
Differential output voltage	V_{DIFFPP}	500	1000	mVp-p	—
Deterministic jitter	J_D	—	0.17	UI p-p	—
Total jitter	J_T	—	0.35	UI p-p	—
Multiple output skew	S_{MO}	—	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit interval	UI	320	320	ps	±100 ppm

Table 62. Long Run Transmitter AC Timing Specifications—1.25 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Output voltage	V_O	–0.40	2.30	V	Voltage relative to COMMON of either signal comprising a differential pair
Differential output voltage	V_{DIFFPP}	800	1600	mVp-p	—
Deterministic jitter	J_D	—	0.17	UI p-p	—
Total jitter	J_T	—	0.35	UI p-p	—
Multiple output skew	S_{MO}	—	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit interval	UI	800	800	ps	±100 ppm

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
$\overline{\text{PCI1\_REQ}}$[4:1]	AH2, AG4, AG3, AH4	I	OV_{DD}	—
				—
				—
				—
				—
$\overline{\text{PCI1\_REQ0}}$	AH3	I/O	OV_{DD}	—
PCI1_CLK	AH26	I	OV_{DD}	39
$\overline{\text{PCI1\_DEVSEL}}$	AH11	I/O	OV_{DD}	2
$\overline{\text{PCI1\_FRAME}}$	AE11	I/O	OV_{DD}	2
PCI1_IDSEL	AG9	I	OV_{DD}	—
$\overline{\text{PCI1\_REQ64}}$/$\overline{\text{PCI2\_FRAME}}$	AF14	I/O	OV_{DD}	2, 5, 10
$\overline{\text{PCI1\_ACK64}}$/$\overline{\text{PCI2\_DEVSEL}}$	V15	I/O	OV_{DD}	2
PCI2_CLK	AE28	I	OV_{DD}	39
$\overline{\text{PCI2\_IRDY}}$	AD26	I/O	OV_{DD}	2
$\overline{\text{PCI2\_PERR}}$	AD25	I/O	OV_{DD}	2
$\overline{\text{PCI2\_GNT}}$[4:1]	AE26, AG24, AF25, AE25	O	OV_{DD}	5, 9, 35
$\overline{\text{PCI2\_GNT0}}$	AG25	I/O	OV_{DD}	—
$\overline{\text{PCI2\_SERR}}$	AD24	I/O	OV_{DD}	2, 4
$\overline{\text{PCI2\_STOP}}$	AF24	I/O	OV_{DD}	2
$\overline{\text{PCI2\_TRDY}}$	AD27	I/O	OV_{DD}	2
$\overline{\text{PCI2\_REQ}}$[4:1]	AD28, AE27, W17, AF26	I	OV_{DD}	—
$\overline{\text{PCI2\_REQ0}}$	AH25	I/O	OV_{DD}	—
DDR SDRAM Memory Interface				
MDQ[0:63]	L18, J18, K14, L13, L19, M18, L15, L14, A17, B17, A13, B12, C18, B18, B13, A12, H18, F18, J14, F15, K19, J19, H16, K15, D17, G16, K13, D14, D18, F17, F14, E14, A7, A6, D5, A4, C8, D7, B5, B4, A2, B1, D1, E4, A3, B2, D2, E3, F3, G4, J5, K5, F6, G5, J6, K4, J1, K2, M5, M3, J3, J2, L1, M6	I/O	GV_{DD}	—
MECC[0:7]	H13, F13, F11, C11, J13, G13, D12, M12	I/O	GV_{DD}	—
MDM[0:8]	M17, C16, K17, E16, B6, C4, H4, K1, E13	O	GV_{DD}	—
MDQS[0:8]	M15, A16, G17, G14, A5, D3, H1, L2, C13	I/O	GV_{DD}	—
$\overline{\text{MDQS}}$[0:8]	L17, B16, J16, H14, C6, C2, H3, L4, D13	I/O	GV_{DD}	—
MA[0:15]	A8, F9, D9, B9, A9, L10, M10, H10, K10, G10, B8, E10, B10, G6, A10, L11	O	GV_{DD}	—
MBA[0:2]	F7, J7, M11	O	GV_{DD}	—

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Clock				
RTC	AF16	I	OV$_{DD}$	—
SYSCLK	AH17	I	OV$_{DD}$	—
JTAG				
TCK	AG28	I	OV$_{DD}$	—
TDI	AH28	I	OV$_{DD}$	12
TDO	AF28	O	OV$_{DD}$	—
TMS	AH27	I	OV$_{DD}$	12
$\overline{\text{TRST}}$	AH23	I	OV$_{DD}$	12
DFT				
L1_TSTCLK	AC25	I	OV$_{DD}$	25
L2_TSTCLK	AE22	I	OV$_{DD}$	25
$\overline{\text{LSSD\_MODE}}$	AH20	I	OV$_{DD}$	25
$\overline{\text{TEST\_SEL}}$	AH14	I	OV$_{DD}$	25
Thermal Management				
THERM0	AG1	—	—	14
THERM1	AH1	—	—	14
Power Management				
ASLEEP	AH18	O	OV$_{DD}$	9, 19, 29
Power and Ground Signals				
GND	A11, B7, B24, C1, C3, C5, C12, C15, C26, D8, D11, D16, D20, D22, E1, E5, E9, E12, E15, E17, F4, F26, G12, G15, G18, G21, G24, H2, H6, H8, H28, J4, J12, J15, J17, J27, K7, K9, K11, K27, L3, L5, L12, L16, N11, N13, N15, N17, N19, P4, P9, P12, P14, P16, P18, R11, R13, R15, R17, R19, T4, T12, T14, T16, T18, U8, U11, U13, U15, U17, U19, V4, V12, V18, W6, W19, Y4, Y9, Y11, Y19, AA6, AA14, AA17, AA22, AA23, AB4, AC2, AC11, AC19, AC26, AD5, AD9, AD22, AE3, AE14, AF6, AF10, AF13, AG8, AG27, K28, L24, L26, N24, N27, P25, R28, T24, T26, U24, V25, W28, Y24, Y26, AA24, AA27, AB25, AC28, L21, L23, N22, P20, R23, T21, U22, V20, W23, Y21, U27	—	—	—
OV$_{DD}$	V16, W11, W14, Y18, AA13, AA21, AB11, AB17, AB24, AC4, AC9, AC21, AD6, AD13, AD17, AD19, AE10, AE8, AE24, AF4, AF12, AF22, AF27, AG26	Power for PCI and other standards (3.3 V)	OV$_{DD}$	—

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
LV_{DD}	N8, R7, T9, U6	Power for TSEC1 and TSEC2 (2.5 V, 3.3 V)	LV_{DD}	—
TV_{DD}	W9, Y6	Power for TSEC3 and TSEC4 (2,5 V, 3.3 V)	TV_{DD}	—
GV_{DD}	B3, B11, C7, C9, C14, C17, D4, D6, D10, D15, E2, E8, E11, E18, F5, F12, F16, G3, G7, G9, G11, H5, H12, H15, H17, J10, K3, K12, K16, K18, L6, M4, M8, M13	Power for DDR1 and DDR2 DRAM I/O voltage (1.8 V, 2.5)	GV_{DD}	—
BV_{DD}	C21, C24, C27, E20, E25, G19, G23, H26, J20	Power for local bus (1.8 V, 2.5 V, 3.3 V)	BV_{DD}	—
V_{DD}	M19, N12, N14, N16, N18, P11, P13, P15, P17, P19, R12, R14, R16, R18, T11, T13, T15, T17, T19, U12, U14, U16, U18, V17, V19	Power for core (1.1 V)	V_{DD}	—
SV_{DD}	L25, L27, M24, N28, P24, P26, R24, R27, T25, V24, V26, W24, W27, Y25, AA28, AC27	Core Power for SerDes transceivers (1.1 V)	SV_{DD}	—
XV_{DD}	L20, L22, N23, P21, R22, T20, U23, V21, W22, Y20	Pad Power for SerDes transceivers (1.1 V)	XV_{DD}	—
AVDD_LBIU	J28	Power for local bus PLL (1.1 V)	—	26
AVDD_PCI1	AH21	Power for PCI1 PLL (1.1 V)	—	26
AVDD_PCI2	AH22	Power for PCI2 PLL (1.1 V)	—	26
AVDD_CORE	AH15	Power for e500 PLL (1.1 V)	—	26
AVDD_PLAT	AH19	Power for CCB PLL (1.1 V)	—	26
AVDD_SRDS	U25	Power for SRDSPLL (1.1 V)	—	26
SENSEVDD	M14	O	V_{DD}	13

Table 72. MPC8547E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
TSEC2_TX_ER	R10	O	LV$_{DD}$	5, 9, 33
Three-Speed Ethernet Controller (Gigabit Ethernet 3)				
TSEC3_TXD[3:0]	V8, W10, Y10, W7	O	TV$_{DD}$	5, 9, 29
TSEC3_RXD[3:0]	Y1, W3, W5, W4	I	TV$_{DD}$	—
TSEC3_GTX_CLK	W8	O	TV$_{DD}$	—
TSEC3_RX_CLK	W2	I	TV$_{DD}$	—
TSEC3_RX_DV	W1	I	TV$_{DD}$	—
TSEC3_RX_ER	Y2	I	TV$_{DD}$	—
TSEC3_TX_CLK	V10	I	TV$_{DD}$	—
TSEC3_TX_EN	V9	O	TV$_{DD}$	30
Three-Speed Ethernet Controller (Gigabit Ethernet 4)				
TSEC4_TXD[3:0]/TSEC3_TXD[7:4]	AB8, Y7, AA7, Y8	O	TV$_{DD}$	1, 5, 9, 29
TSEC4_RXD[3:0]/TSEC3_RXD[7:4]	AA1, Y3, AA2, AA4	I	TV$_{DD}$	1
TSEC4_GTX_CLK	AA5	O	TV$_{DD}$	
TSEC4_RX_CLK/TSEC3_COL	Y5	I	TV$_{DD}$	1
TSEC4_RX_DV/TSEC3_CRS	AA3	I/O	TV$_{DD}$	1, 31
TSEC4_TX_EN/TSEC3_TX_ER	AB6	O	TV$_{DD}$	1, 30
DUART				
$\overline{\text{UART\_CTS}}$[0:1]	AB3, AC5	I	OV$_{DD}$	—
$\overline{\text{UART\_RTS}}$[0:1]	AC6, AD7	O	OV$_{DD}$	—
UART_SIN[0:1]	AB5, AC7	I	OV$_{DD}$	—
UART_SOUT[0:1]	AB7, AD8	O	OV$_{DD}$	—
I^{2}C Interface				
IIC1_SCL	AG22	I/O	OV$_{DD}$	4, 27
IIC1_SDA	AG21	I/O	OV$_{DD}$	4, 27
IIC2_SCL	AG15	I/O	OV$_{DD}$	4, 27
IIC2_SDA	AG14	I/O	OV$_{DD}$	4, 27
SerDes				
SD_RX[0:3]	M28, N26, P28, R26	I	XV$_{DD}$	—
$\overline{\text{SD\_RX}}$[0:3]	M27, N25, P27, R25	I	XV$_{DD}$	—
SD_TX[0:3]	M22, N20, P22, R20	O	XV$_{DD}$	—
$\overline{\text{SD\_TX}}$[0:3]	M23, N21, P23, R21	O	XV$_{DD}$	—
Reserved	W26, Y28, AA26, AB28	—	—	40
Reserved	W25, Y27, AA25, AB27	—	—	40

Table 74. MPC8543E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
$\overline{\text{PCI1\_TRDY}}$	AG11	I/O	OV_{DD}	2
$\overline{\text{PCI1\_REQ}}$[4:1]	AH2, AG4, AG3, AH4	I	OV_{DD}	—
$\overline{\text{PCI1\_REQ0}}$	AH3	I/O	OV_{DD}	—
PCI1_CLK	AH26	I	OV_{DD}	39
$\overline{\text{PCI1\_DEVSEL}}$	AH11	I/O	OV_{DD}	2
$\overline{\text{PCI1\_FRAME}}$	AE11	I/O	OV_{DD}	2
PCI1_IDSEL	AG9	I	OV_{DD}	—
cfg_pci1_width	AF14	I/O	OV_{DD}	112
Reserved	V15	—	—	110
Reserved	AE28	—	—	2
Reserved	AD26	—	—	110
Reserved	AD25	—	—	110
Reserved	AE26	—	—	110
cfg_pci1_clk	AG24	I	OV_{DD}	5
Reserved	AF25	—	—	101
Reserved	AE25	—	—	110
Reserved	AG25	—	—	110
Reserved	AD24	—	—	110
Reserved	AF24	—	—	110
Reserved	AD27	—	—	110
Reserved	AD28, AE27, W17, AF26	—	—	110
Reserved	AH25	—	—	110
DDR SDRAM Memory Interface				
MDQ[0:63]	L18, J18, K14, L13, L19, M18, L15, L14, A17, B17, A13, B12, C18, B18, B13, A12, H18, F18, J14, F15, K19, J19, H16, K15, D17, G16, K13, D14, D18, F17, F14, E14, A7, A6, D5, A4, C8, D7, B5, B4, A2, B1, D1, E4, A3, B2, D2, E3, F3, G4, J5, K5, F6, G5, J6, K4, J1, K2, M5, M3, J3, J2, L1, M6	I/O	GV_{DD}	—
MECC[0:7]	H13, F13, F11, C11, J13, G13, D12, M12	I/O	GV_{DD}	—
MDM[0:8]	M17, C16, K17, E16, B6, C4, H4, K1, E13	O	GV_{DD}	—
MDQS[0:8]	M15, A16, G17, G14, A5, D3, H1, L2, C13	I/O	GV_{DD}	—
$\overline{\text{MDQS}}$[0:8]	L17, B16, J16, H14, C6, C2, H3, L4, D13	I/O	GV_{DD}	—
MA[0:15]	A8, F9, D9, B9, A9, L10, M10, H10, K10, G10, B8, E10, B10, G6, A10, L11	O	GV_{DD}	—
MBA[0:2]	F7, J7, M11	O	GV_{DD}	—

21 Thermal

This section describes the thermal specifications of the device.

21.1 Thermal for Version 2.0 Silicon HiCTE FC-CBGA with Full Lid

This section describes the thermal specifications for the HiCTE FC-CBGA package for revision 2.0 silicon.

This table shows the package thermal characteristics.

Table 84. Package Thermal Characteristics for HiCTE FC-CBGA

Characteristic	JEDEC Board	Symbol	Value	Unit	Notes
Die junction-to-ambient (natural convection)	Single-layer board (1s)	$R_{\theta JA}$	17	°C/W	1, 2
Die junction-to-ambient (natural convection)	Four-layer board (2s2p)	$R_{\theta JA}$	12	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Single-layer board (1s)	$R_{\theta JA}$	11	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Four-layer board (2s2p)	$R_{\theta JA}$	8	°C/W	1, 2
Die junction-to-board	N/A	$R_{\theta JB}$	3	°C/W	3
Die junction-to-case	N/A	$R_{\theta JC}$	0.8	°C/W	4

Notes:

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, airflow, power dissipation of other components on the board, and board thermal resistance.
2. Per JEDEC JESD51-6 with the board (JESD51-7) horizontal.
3. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
4. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1). The cold plate temperature is used for the case temperature, measured value includes the thermal resistance of the interface layer.

21.2 Thermal for Version 2.1.1, 2.1.2, and 2.1.3 Silicon FC-PBGA with Full Lid and Version 3.1.x Silicon with Stamped Lid

This section describes the thermal specifications for the FC-PBGA package for revision 2.1.1, 2.1.2, and 3.0 silicon.

This table shows the package thermal characteristics.

Table 85. Package Thermal Characteristics for FC-PBGA

Characteristic	JEDEC Board	Symbol	Value	Unit	Notes
Die junction-to-ambient (natural convection)	Single-layer board (1s)	$R_{\theta JA}$	18	°C/W	1, 2
Die junction-to-ambient (natural convection)	Four-layer board (2s2p)	$R_{\theta JA}$	13	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Single-layer board (1s)	$R_{\theta JA}$	13	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Four-layer board (2s2p)	$R_{\theta JA}$	9	°C/W	1, 2